

Transmittal Letter filed herewith. A clean copy of the claims as amended is appended hereto.

Kindly enter the following amendments:

IN THE CLAIMS:

Please amend Claims 1 and 8 as follows:

Sub h1 1. (Four Times Amended) A method for forming a semiconductor device having a laminated structure including a dielectric film made from a metal oxide formed on a surface of a heated substrate and a CVD high melting point metal nitride film [directly formed thereover], wherein said metal nitride film is directly formed on said dielectric film by introducing a source gas containing said high melting point metal into a chamber in which said substrate is contained,

said method comprising a step of [treating] heating said substrate in an ambient that is non-reactive with respect to said metal oxide formed on said surface of said substrate in said chamber wherein said non-reactive ambient includes at least one of a gas non-reactive with respect to said metal oxide contained in said dielectric film and NH_3 gas, and

introducing into said chamber a source gas for forming said CVD-TiN film and NH_3 gas, following said heating step, and further

wherein a temperature of said substrate is set at a prescribed temperature, before said source gas containing said high melting point metal is introduced into said chamber.